

64K x 24 Static RAM Module

Features

- High-density 1.5M SRAM module
- High-speed CMOS SRAMs
 - Access time of 25 ns
- 56-pin, 0.5-inch-high ZIP package
- Low active power
 - 2.8W (max. for $t_{AA} = 25$ ns)
- SMD technology
- TTL-compatible inputs and outputs
- Commercial temperature range
- Small PCB footprint
 - 1.05 sq. in.

using six 32K x 8 static RAMs in SOJ packages mounted onto an epoxy laminate board with pins.

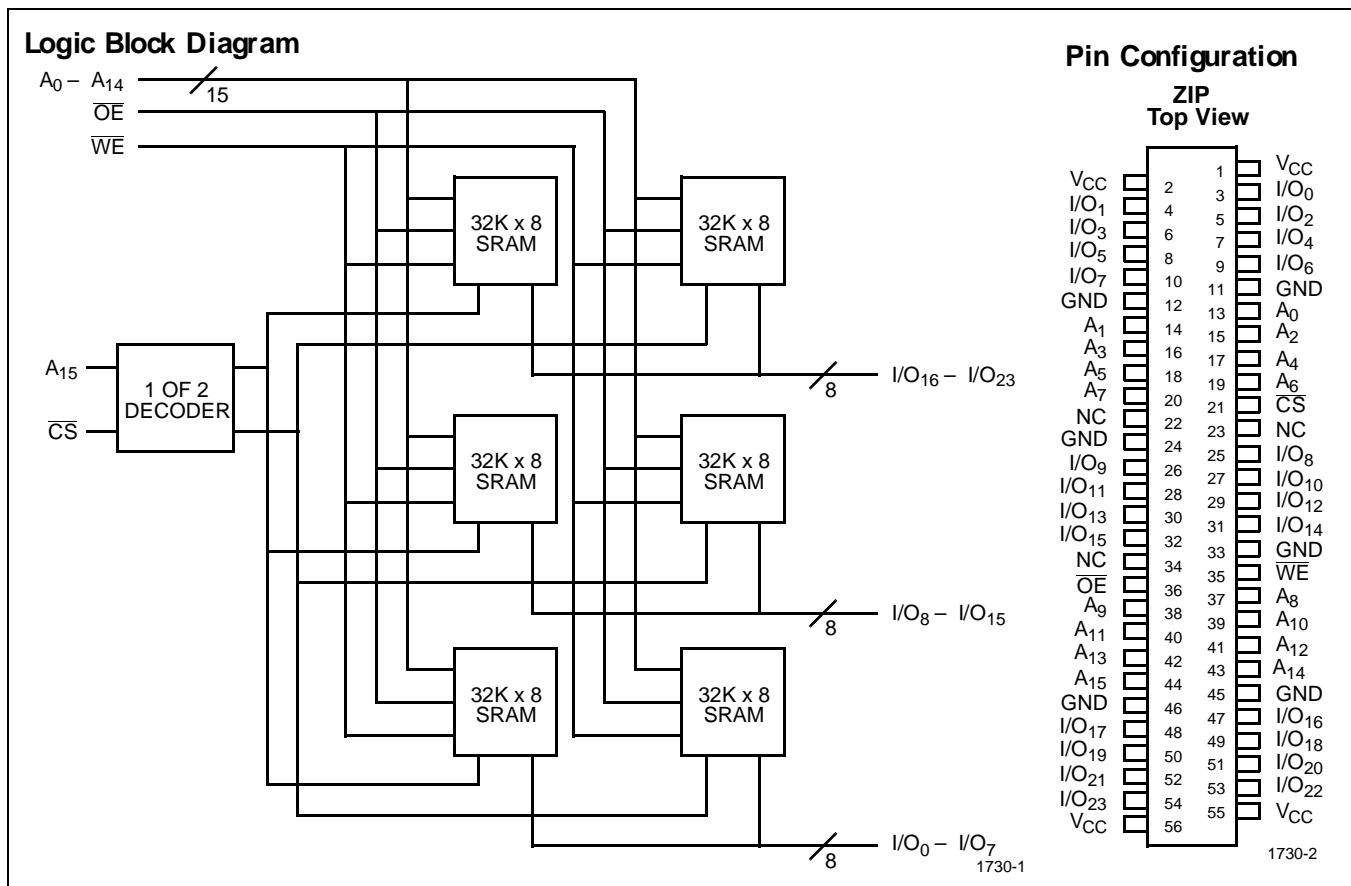
Writing to the device is accomplished when the chip select (\overline{CS}) and write enable (\overline{WE}) inputs are both LOW. Data on the input/output pins (I/O_0 through I/O_{23}) of the device is written into the memory location specified on the address pins (A_0 through A_{15}).

Reading the device is accomplished by taking the chip select (\overline{CS}) and output enable (\overline{OE}) LOW while write enable (\overline{WE}) remains HIGH. Under these conditions, the contents of the memory location specified on the address pins will appear on the input/output pins.

The input/output pins remain in a high-impedance state unless the module is selected, outputs are enabled, and write enable is HIGH.

Functional Description

The CYM1730 is a high-performance 1.5M static RAM module organized as 64K words by 24 bits. This module is constructed



Selection Guide

| | 1730-25 | 1730-30 | 1730-35 |
|--------------------------------|---------|---------|---------|
| Maximum Access Time (ns) | 25 | 30 | 35 |
| Maximum Operating Current (mA) | 510 | 510 | 510 |
| Maximum Standby Current (mA) | 180 | 180 | 180 |

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature -55°C to +125°C

Ambient Temperature with Power Applied..... -10°C to +85°C

Supply Voltage to Ground Potential -0.5V to +7.0V

DC Voltage Applied to Outputs in High Z State -0.5V to +7.0V

DC Input Voltage -0.5V to +7.0V

Operating Range

| Range | Ambient Temperature | V _{CC} |
|------------|---------------------|-----------------|
| Commercial | 0°C to +70°C | 5V ± 10% |

Electrical Characteristics Over the Operating Range

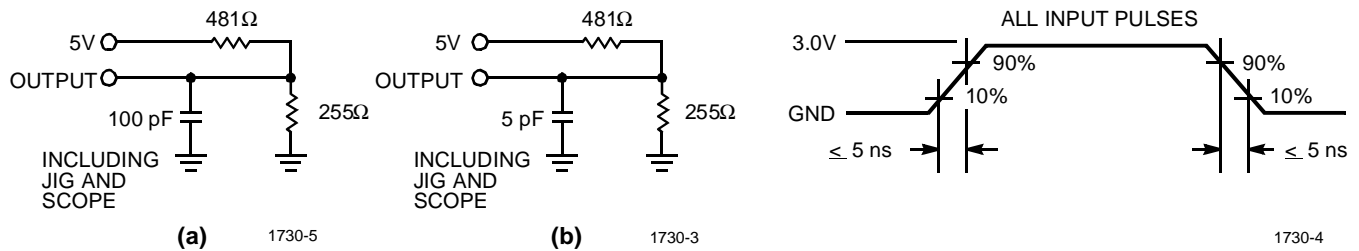
| Parameter | Description | Test Conditions | Min. | Max. | Unit |
|------------------|---|--|------|-----------------------|------|
| V _{OH} | Output HIGH Voltage | V _{CC} = Min., I _{OH} = -4.0 mA | 2.4 | | V |
| V _{OL} | Output LOW Voltage | V _{CC} = Min., I _{OL} = 8.0 mA | | 0.4 | V |
| V _{IH} | Input HIGH Voltage | | 2.2 | V _{CC} + 0.3 | V |
| V _{IL} | Input LOW Voltage | | -0.3 | 0.8 | V |
| I _{IX} | Input Load Current | GND ≤ V _I ≤ V _{CC} | -20 | +20 | μA |
| I _{OZ} | Output Leakage Current | GND ≤ V _O ≤ V _{CC} , Output Disabled | -10 | +10 | μA |
| I _{CC} | V _{CC} Operating Supply Current | V _{CC} = Max., I _{OUT} = 0 mA, $\overline{CS} \leq V_{IL}$ | | 510 | mA |
| I _{SB1} | Automatic \overline{CS} Power-Down Current ^[1] | Max. V _{CC} , $\overline{CS} \geq V_{IH}$, Min. Duty Cycle = 100% | | 180 | mA |
| I _{SB2} | Automatic \overline{CS} Power-Down Current ^[1] | Max. V _{CC} , $\overline{CS} \geq V_{CC} - 0.2V$, V _{IN} ≥ V _{CC} - 0.2V or V _{IN} ≤ 0.2V | | 180 | mA |

Capacitance^[2]

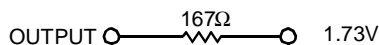
| Parameter | Description | Test Conditions | Max. | Unit |
|------------------|--------------------|-----------------------------------|------|------|
| C _{IN} | Input Capacitance | T _A = 25°C, f = 1 MHz, | 50 | pF |
| C _{OUT} | Output Capacitance | V _{CC} = 5.0V | 20 | pF |

Notes:

1. A pull-up resistor to V_{CC} on the \overline{CS} input is required to keep the device deselected during V_{CC} power-up, otherwise I_{SB} will exceed values given.
2. Tested on a sample basis.

AC Test Loads and Waveforms


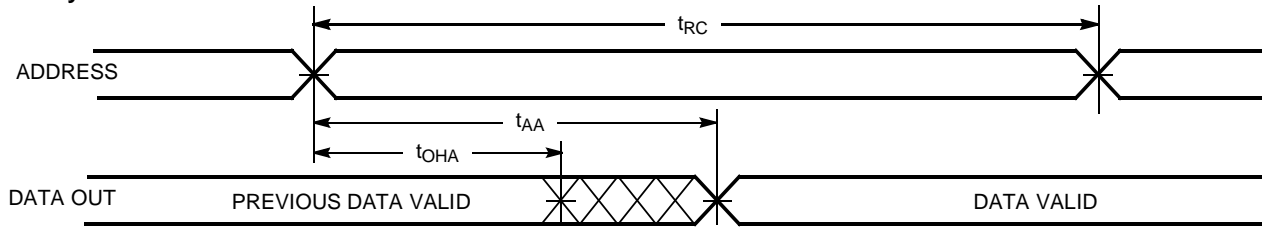
Equivalent to: THÉVENIN EQUIVALENT


Switching Characteristics Over the Operating Range^[3]

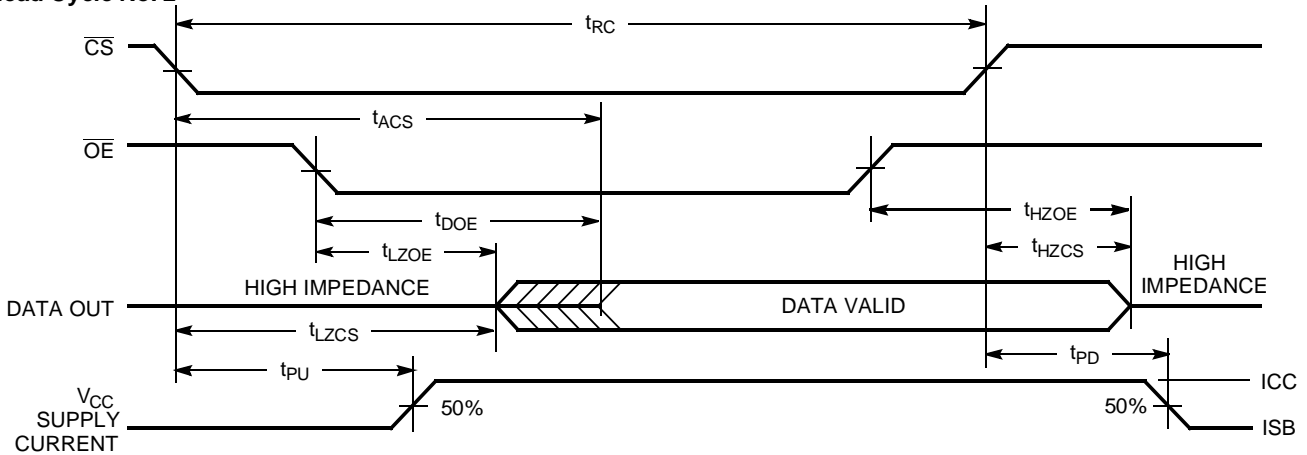
| Parameter | Description | 1730-25 | | 1730-30 | | 1730-35 | | Unit |
|----------------------------------|--|---------|------|---------|------|---------|------|------|
| | | Min. | Max. | Min. | Max. | Min. | Max. | |
| READ CYCLE | | | | | | | | |
| t_{RC} | Read Cycle Time | 25 | | 30 | | 35 | | ns |
| t_{AA} | Address to Data Valid | | 25 | | 30 | | 35 | ns |
| t_{OHA} | Output Hold from Address Change | 5 | | 5 | | 5 | | ns |
| t_{ACS} | \overline{CS} LOW to Data Valid | | 25 | | 30 | | 35 | ns |
| t_{DOE} | \overline{OE} LOW to Data Valid | | 12 | | 15 | | 20 | ns |
| t_{LZOE} | \overline{OE} LOW to Low Z | 3 | | 3 | | 3 | | ns |
| t_{HZOE} | \overline{OE} HIGH to High Z | | 10 | | 15 | | 20 | ns |
| t_{LZCS} | \overline{CS} LOW to Low Z ^[4] | 5 | | 5 | | 5 | | ns |
| t_{HZCS} | \overline{CS} HIGH to High Z ^[4, 5] | | 10 | | 15 | | 15 | ns |
| WRITE CYCLE^[6] | | | | | | | | |
| t_{WC} | Write Cycle Time | 25 | | 30 | | 35 | | ns |
| t_{SCS} | \overline{CS} LOW to Write End | 20 | | 25 | | 30 | | ns |
| t_{AW} | Address Set-Up to Write End | 22 | | 25 | | 30 | | ns |
| t_{HA} | Address Hold from Write End | 2 | | 2 | | 2 | | ns |
| t_{SA} | Address Set-Up to Write Start | 2 | | 2 | | 2 | | ns |
| t_{PWE} | \overline{WE} Pulse Width | 20 | | 23 | | 25 | | ns |
| t_{SD} | Data Set-Up to Write End | 13 | | 15 | | 20 | | ns |
| t_{HD} | Data Hold from Write End | 2 | | 2 | | 2 | | ns |
| t_{LZWE} | \overline{WE} HIGH to Low Z | 3 | | 3 | | 5 | | ns |
| t_{HZWE} | \overline{WE} LOW to High Z ^[5] | 0 | 10 | 0 | 10 | 0 | 15 | ns |

Notes:

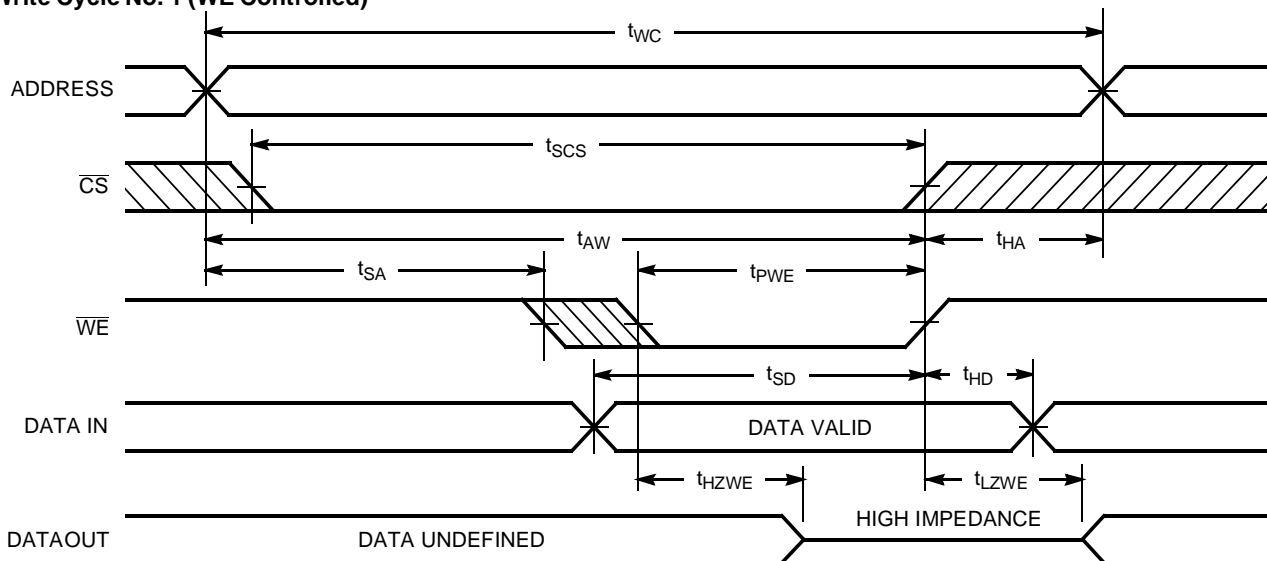
- Test conditions assume signal transition time of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
- At any given temperature and voltage condition, t_{HZCS} is less than t_{LZCS} for any given device.
- t_{HZOE} , t_{HZCS} , and t_{LZCE} are specified with $C_L = 5$ pF as in part (b) of AC Test Loads and Waveforms. Transition is measured ± 500 mV from steady-state voltage.
- The internal write time of the memory is defined by the overlap of \overline{CS} LOW and \overline{WE} LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.

Switching Waveforms
Read Cycle No. 1 [7, 8]


1730-6

Read Cycle No. 2 [7, 9]


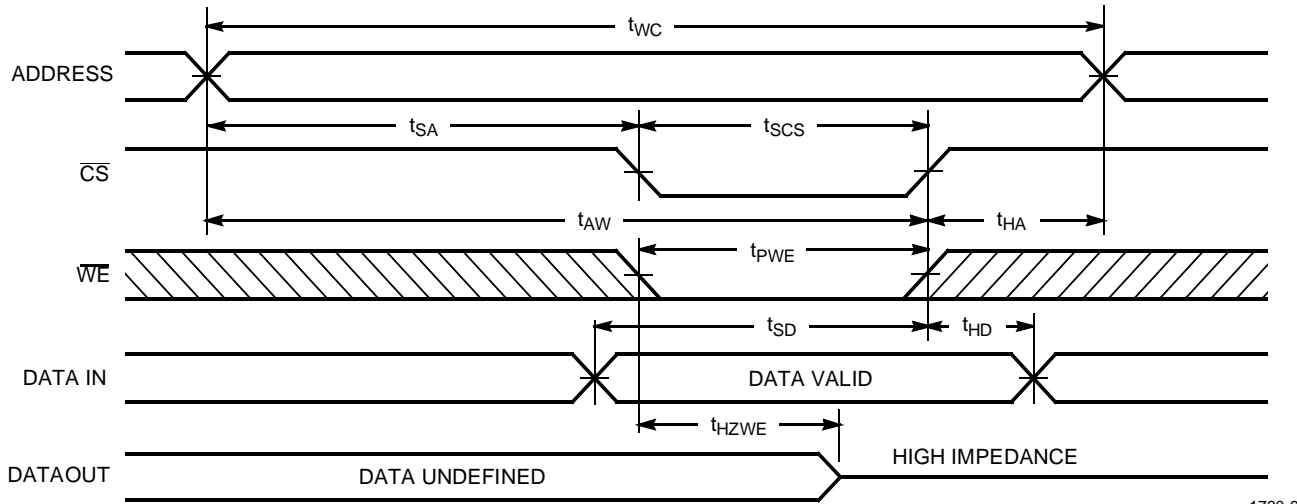
1730-7

Write Cycle No. 1 (WE Controlled) [6, 10]


1730-8

Notes:

7. \overline{WE} is HIGH for read cycle.
8. Device is continuously selected, $\overline{CS} = V_{IL}$ and $\overline{OE} = V_{IL}$.
9. Address valid prior to or coincident with \overline{CS} transition LOW.
10. Data I/O will be high impedance if $\overline{OE} = V_{IH}$.

Switching Waveforms (continued)
Write Cycle No. 2 (\overline{CS} Controlled) [6, 10, 11]


1730-9

Note:

11. If
- \overline{CS}
- goes HIGH simultaneously with
- \overline{WE}
- HIGH, the output remains in a high-impedance state.

Truth Table

| \overline{CS} | \overline{WE} | \overline{OE} | Input/Outputs | Mode |
|-----------------|-----------------|-----------------|---------------|---------------------|
| H | X | X | High Z | Deselect/Power-Down |
| L | H | L | Data Out | Read Word |
| L | L | X | Data In | Write Word |
| L | H | H | High Z | Deselect |

Ordering Information

| Speed (ns) | Ordering Code | Package Name | Package Type | Operating Range |
|------------|---------------|--------------|-------------------|-----------------|
| 25 | CYM1730PZ-25C | PZ07 | 56-Pin ZIP Module | Commercial |
| 30 | CYM1730PZ-30C | PZ07 | 56-Pin ZIP Module | Commercial |
| 35 | CYM1730PZ-35C | PZ07 | 56-Pin ZIP Module | Commercial |

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Package Diagram

56-Pin ZIP Module PZ07

